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(54) Title: A METHOD OF INITIATING MOLECULAR BONDING

(57) Abstract: The invention relates to a method of initiating molecular bonding, comprising bringing one face (31) of a first wafer (30) to face one face (21) of a second wafer (20) and initiating a point of contact between the two facing faces. The point of contact is initiated by application to one of the two wafers, for example using a bearing element (51) of a tool (50), of a mechanical pressure in the range 0,1 MPa to 33.3 MPa.

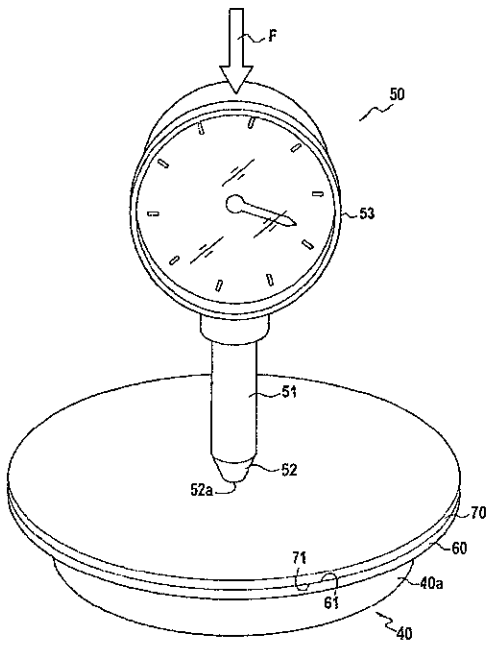


FIG.2

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